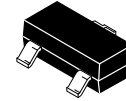


PNP Darlington Transistor

BCV26



SOT-23
CASE 318

Description

This device is designed for applications requiring extremely high current gain at collector currents to 800 mA. Sourced from Process 61.

ABSOLUTE MAXIMUM RATINGS

($T_A = 25^\circ\text{C}$ unless otherwise noted.) (Notes 1, 2, 3)

Symbol	Parameter	Value	Unit
V_{CEO}	Collector-Emmitter Voltage	30	V
V_{CBO}	Collector-Base Voltage	40	V
V_{EBO}	Emitter-Base Voltage	10	V
I_C	Collector Current - Continuous	1.2	A
T_J, T_{STG}	Operating and Storage Junction Temperature Range	-55 to +150	$^\circ\text{C}$

Stresses exceeding those listed in the Maximum Ratings table may damage the device. If any of these limits are exceeded, device functionality should not be assumed, damage may occur and reliability may be affected.

- These ratings are based on a maximum junction temperature of 150°C .
- These are steady-state limits. onsemi should be consulted on applications involving pulsed or low-duty-cycle operations.
- All voltages (V) and currents (A) are negative polarity for PNP transistors.

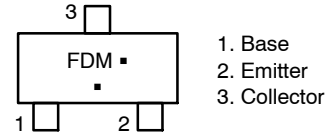
THERMAL CHARACTERISTICS

($T_A = 25^\circ\text{C}$ unless otherwise noted.) (Note 4)

Symbol	Parameter	Max	Unit
P_D	Total Device Dissipation	350	mW
	Derate Above 25°C	2.8	mW/ $^\circ\text{C}$
$R_{\theta JA}$	Thermal Resistance, Junction-to-Ambient	357	$^\circ\text{C}/\text{W}$

- Device mounted on FR-4 PCB 40 mm x 40 mm x 1.5 mm.

MARKING DIAGRAM



FD = Specific Device Code
M = Date Code
▪ = Pb-Free Package

(Note: Microdot may be in either location)

ORDERING INFORMATION

Device	Package	Shipping
BCV26	SOT-23 (Pb-Free, Halide Free)	3,000 / Tape & Reel

†For information on tape and reel specifications, including part orientation and tape sizes, please refer to our Tape and Reel Packaging Specification Brochure, BRD8011/D.

BCV26

ELECTRICAL CHARACTERISTICS ($T_A = 25^\circ\text{C}$ unless otherwise noted.)

Symbol	Parameter	Test Conditions	Min	Typ	Max	Unit
--------	-----------	-----------------	-----	-----	-----	------

OFF CHARACTERISTICS

$V_{(BR)CEO}$	Collector–Emitter Breakdown Voltage	$I_C = 10\text{ mA}, I_B = 0$	30	–	–	V
$V_{(BR)CBO}$	Collector–Base Breakdown Voltage	$I_C = 10\ \mu\text{A}, I_E = 0$	40	–	–	V
$V_{(BR)EBO}$	Emitter–Base Breakdown Voltage	$I_E = 100\text{ nA}, I_C = 0$	10	–	–	V
I_{CBO}	Collector Cut–Off Current	$V_{CB} = 30\text{ V}, I_E = 0$	–	–	0.1	μA
I_{EBO}	Emitter Cut–Off Current	$V_{EB} = 10\text{ V}, I_C = 0$	–	–	0.1	μA

ON CHARACTERISTICS

h_{FE}	DC Current Gain	$I_C = 1.0\text{ mA}, V_{CE} = 5.0\text{ V}$	4000	–	–	
		$I_C = 10\text{ mA}, V_{CE} = 5.0\text{ V}$	10000	–	–	
		$I_C = 100\text{ mA}, V_{CE} = 5.0\text{ V}$	20000	–	–	
$V_{CE(sat)}$	Collector–Emitter Saturation Voltage	$I_C = 100\text{ mA}, I_B = 0.1\text{ mA}$	–	–	1.0	V
$V_{BE(sat)}$	Base–Emitter Saturation Voltage	$I_C = 100\text{ mA}, I_B = 0.1\text{ mA}$	–	–	1.5	V

SMALL SIGNAL CHARACTERISTICS

f_T	Current Gain – Bandwidth Product	$I_C = 30\text{ mA}, V_{CE} = 5.0\text{ V}, f = 100\text{ MHz}$	–	220	–	MHz
C_C	Collector Capacitance	$V_{CB} = 30\text{ V}, I_E = 0, f = 1.0\text{ MHz}$	–	3.5	–	pF

Product parametric performance is indicated in the Electrical Characteristics for the listed test conditions, unless otherwise noted. Product performance may not be indicated by the Electrical Characteristics if operated under different conditions.

NOTE: All voltages (V) and currents (A) are negative polarity for PNP transistors.

TYPICAL CHARACTERISTICS

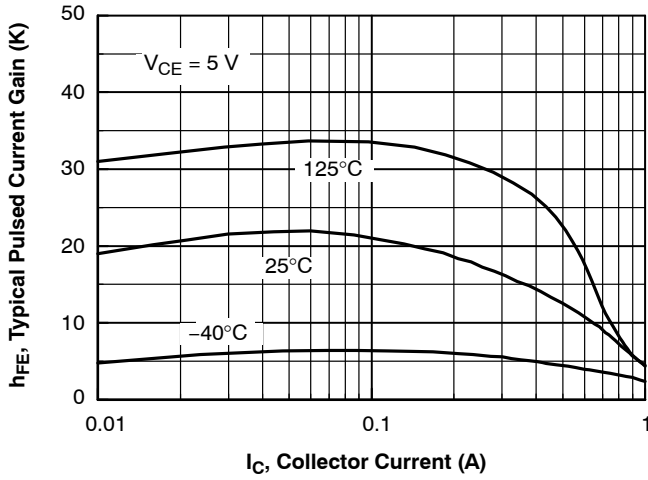


Figure 1. Typical Pulsed Current Gain vs. Collector Current

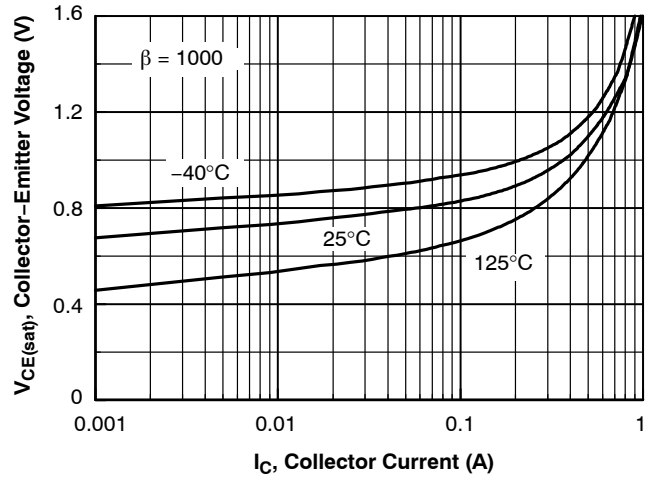


Figure 2. Collector-Emitter Saturation Voltage vs. Collector Current

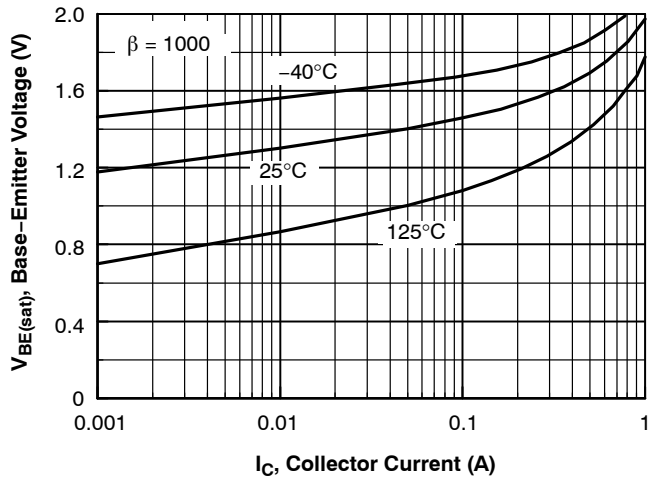


Figure 3. Base-Emitter Saturation Voltage vs. Collector Current

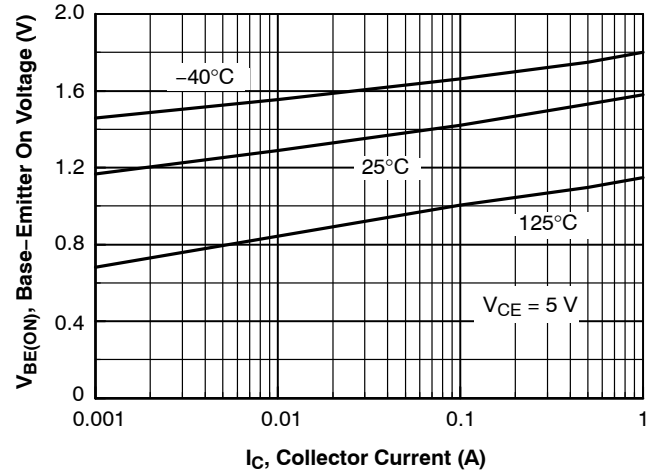


Figure 4. Base Emitter On Voltage vs. Collector Current

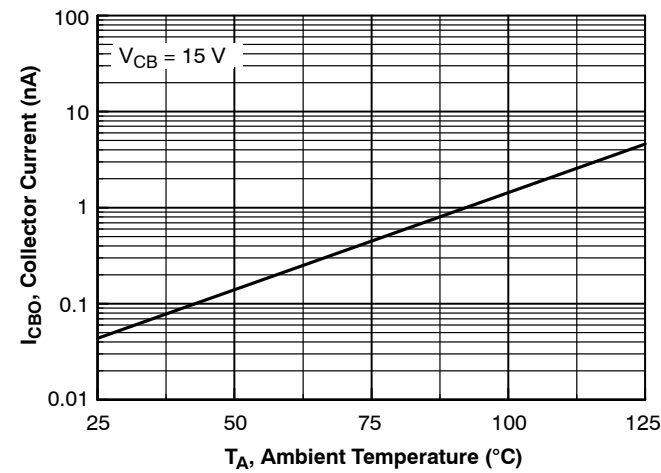


Figure 5. Collector Cut-Off Current vs. Ambient Temperature

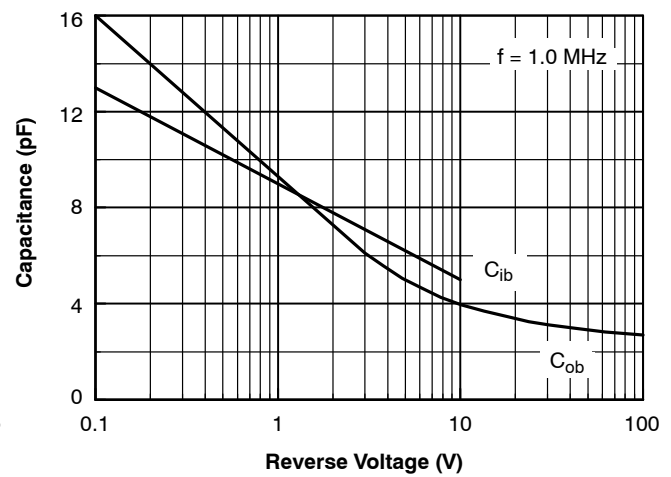


Figure 6. Input and Output Capacitance vs. Reverse Bias Voltage

TYPICAL CHARACTERISTICS (Continued)

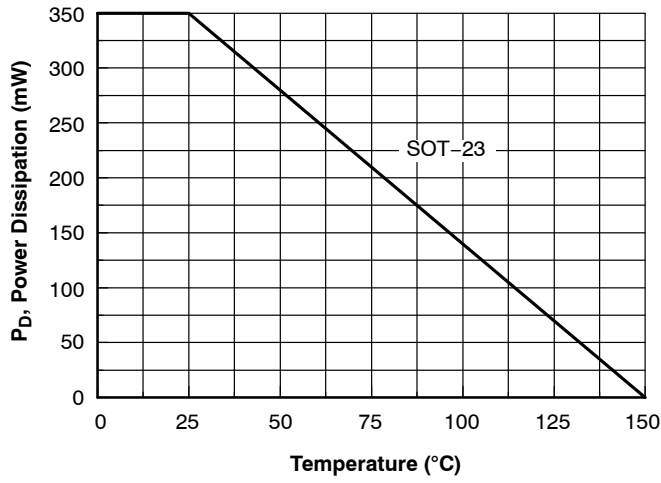


Figure 7. Power Dissipation vs. Ambient Temperature

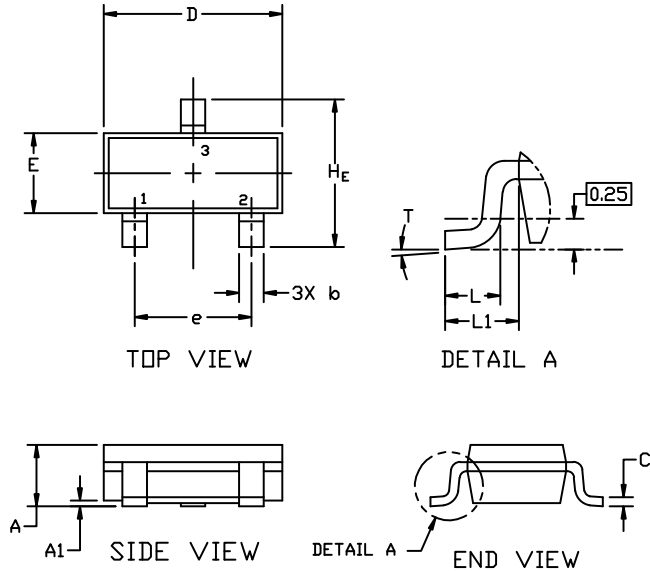
MECHANICAL CASE OUTLINE PACKAGE DIMENSIONS



SOT-23 (TO-236)
CASE 318
ISSUE AT

DATE 01 MAR 2023

SCALE 4:1

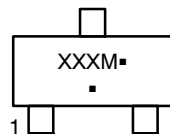


NOTES:

1. DIMENSIONING AND TOLERANCING PER ASME Y14.5M,1994.
2. CONTROLLING DIMENSION: MILLIMETERS
3. MAXIMUM LEAD THICKNESS INCLUDES LEAD FINISH. MINIMUM LEAD THICKNESS IS THE MINIMUM THICKNESS OF THE BASE MATERIAL.
4. DIMENSIONS D AND E DO NOT INCLUDE MOLD FLASH, PROTRUSIONS, OR GATE BURRS.

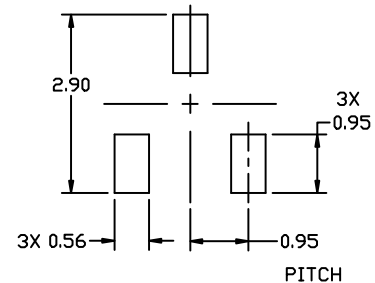
DIM	MILLIMETERS			INCHES		
	MIN.	NOM.	MAX.	MIN.	NOM.	MAX.
A	0.89	1.00	1.11	0.035	0.039	0.044
A1	0.01	0.06	0.10	0.000	0.002	0.004
b	0.37	0.44	0.50	0.015	0.017	0.020
c	0.08	0.14	0.20	0.003	0.006	0.008
D	2.80	2.90	3.04	0.110	0.114	0.120
E	1.20	1.30	1.40	0.047	0.051	0.055
e	1.78	1.90	2.04	0.070	0.075	0.080
L	0.30	0.43	0.55	0.012	0.017	0.022
L1	0.35	0.54	0.69	0.014	0.021	0.027
H _E	2.10	2.40	2.64	0.083	0.094	0.104
T	0°	---	10°	0°	---	10°

GENERIC MARKING DIAGRAM*



- XXX = Specific Device Code
- M = Date Code
- = Pb-Free Package

*This information is generic. Please refer to device data sheet for actual part marking. Pb-Free indicator, "G" or microdot "▪", may or may not be present. Some products may not follow the Generic Marking.



RECOMMENDED MOUNTING FOOTPRINT

* For additional information on our Pb-Free strategy and soldering details, please download the ON Semiconductor Soldering and Mounting Techniques Reference Manual, SOLDERRM/D.

STYLES ON PAGE 2

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MECHANICAL CASE OUTLINE

PACKAGE DIMENSIONS



SOT-23 (TO-236) CASE 318 ISSUE AT

DATE 01 MAR 2023

- | | | | | | |
|---|---|---|---|---|---|
| STYLE 1 THRU 5:
CANCELLED | STYLE 6:
PIN 1. BASE
2. EMITTER
3. COLLECTOR | STYLE 7:
PIN 1. EMITTER
2. BASE
3. COLLECTOR | STYLE 8:
PIN 1. ANODE
2. NO CONNECTION
3. CATHODE | | |
| STYLE 9:
PIN 1. ANODE
2. ANODE
3. CATHODE | STYLE 10:
PIN 1. DRAIN
2. SOURCE
3. GATE | STYLE 11:
PIN 1. ANODE
2. CATHODE
3. CATHODE-ANODE | STYLE 12:
PIN 1. CATHODE
2. CATHODE
3. ANODE | STYLE 13:
PIN 1. SOURCE
2. DRAIN
3. GATE | STYLE 14:
PIN 1. CATHODE
2. GATE
3. ANODE |
| STYLE 15:
PIN 1. GATE
2. CATHODE
3. ANODE | STYLE 16:
PIN 1. ANODE
2. CATHODE
3. CATHODE | STYLE 17:
PIN 1. NO CONNECTION
2. ANODE
3. CATHODE | STYLE 18:
PIN 1. NO CONNECTION
2. CATHODE
3. ANODE | STYLE 19:
PIN 1. CATHODE
2. ANODE
3. CATHODE-ANODE | STYLE 20:
PIN 1. CATHODE
2. ANODE
3. GATE |
| STYLE 21:
PIN 1. GATE
2. SOURCE
3. DRAIN | STYLE 22:
PIN 1. RETURN
2. OUTPUT
3. INPUT | STYLE 23:
PIN 1. ANODE
2. ANODE
3. CATHODE | STYLE 24:
PIN 1. GATE
2. DRAIN
3. SOURCE | STYLE 25:
PIN 1. ANODE
2. CATHODE
3. GATE | STYLE 26:
PIN 1. CATHODE
2. ANODE
3. NO CONNECTION |
| STYLE 27:
PIN 1. CATHODE
2. CATHODE
3. CATHODE | STYLE 28:
PIN 1. ANODE
2. ANODE
3. ANODE | | | | |

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